

Substitute for form 1449B/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Application Number	10/608,432
		Filing Date	06/30/2003
		First Named Inventor	Robert BELLMAN
		Group Art Unit	2874
		Examiner Name	Unassigned
		Attorney Docket Number	064951-0204
Sheet	2 of 3		

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
hnh	A16	ARNOLDBIK et al., "Dynamic Behavior of Hydrogen in Silicon Nitride and Oxynitride Films Made by Low-Pressure Chemical Vapor Deposition", The American Physical Society, Physical Review B, Vol. 48, No. 8, Aug. 15, 1993, pp. 5444-5456	
	A17	BOGATYRJOV et al., "Passive Selective Filter for Flattening the Erbium-Doped Fibre Amplifier Gain Spectrum Based on a Feature of the Silicon Oxynitride Fibre Absorption Spectrum", Electronics Letters, Vol. 31, No. 1, Jan. 5, 1995, pp. 61-62	
	A18	BONA et al., "Wavelength Division Multiplexed Add/Drop Ring Technology in Corporate Backbone Networks", Optical Engineering, Vol. 37, No. 12, Dec. 1998, pp. 3218-3228	
	A19	BOSSEBOEUF and BOUCHIER, "Mechanisms of Reactive Ion-Beam Sputtering of Silicon Nitride in Presence of ¹⁵ N- or D-Labeled Ammonia," J. Electrochem. Society, Vol. 133, No. 4, April 1986, pp. 810-816	
	A20	CAVALLARI et al., "Plasma Processing for Silicon Oxynitride Films", J. Electrochem. Soc., Vol. 134, No. 5, May 1987, pp. 1265-1270	
	A21	DENISSE et al., "Annealing of Plasma Silicon Oxynitride Films", J. Appl. Phys., Vol. 60, No. 7, Oct. 1, 1986, pp 2543-2547	
	A22	GERMAN et al., "Silicon-oxynitride Layers for Optical Waveguide Applications," <u>Electrochemical Society Proceedings</u> , Vol. 99-6	
	A23	HABRAKEN et al., "Hydrogen in low-pressure chemical-vapor-deposited silicon (oxy)nitride films," <u>J. Appl. Phys.</u> , January 15, 1986, Vol. 59, No. 2	
	A24	HABRAKEN et al., "Hydrogen in Low-Pressure Chemical-Vapor-Deposited Silicon (Oxy)Nitride Films", J. Appl. Phys. Vol. 59, No. 2, Jan. 15, 1986, pp. 447-453	
	A25	HE et al., "Hydrogen Behavior in PECVD Nitride by SiH ₄ & ND ₃ During RTA," Mat. Res. Soc. Symp. Proc., Vol. 424, Apr. 8-12, 1996, San Francisco, CA pp. 109-114	
	A26	HUBNER, "Strong Bragg Gratings Induced with 248 nm Light in Buried Silicon Oxynitride Waveguides," XP-000987165	
	A27	OHRING, "The Materials Science of Thin Films", 1992, pp. 181-184	
✓	A28	SPEAKMAN et al., "Characterization of PECVD Deposited Silicon Oxynitride Thin Films", Vacuum, Vol. 38, No. 3, 1988, pp. 183-188	

Examiner Signature	<i>Hae Moon Hyun</i>	Date Considered	12-3-04
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Sheet	3	of	3
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**Examiner
Signature**

Hae Moon Hyun

Date Considered

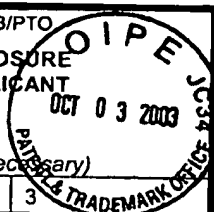
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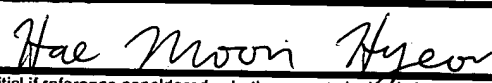
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U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
hnh	A1	4,962,065		BROWN et al.	10-09-1990	
	A2	5,062,680		IMAMURA et al.	11-05-1991	
	A3	5,264,724	A	BROWN et al.	1-23-1993	
	A4	5,343,544	A	BOYD et al.	08-30-1994	
	A5	5,694,513	A	OKANIWA	12-02-1997	
	A6	5,979,188	A	OJHA	11-09-1999	
	A7	5,972,765	A	CLARK et al.	11-26-1999	
	A8	6,077,791	A	DeTAR	06-20-2000	
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	A12	6,499,318	B1	LEMAIRE et al.	12-31-2002	

FOREIGN PATENT DOCUMENTS								
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		Office ³	Number ⁴	Kind Code ⁵ (if known)				
hnh	A13	WO	01/64594	A1	INTERNATIONAL BUSINESS MACHINES CORPORATION	09-07-2001		
hnh	A14	JP	09-078244		CANON INC.	03-25-1997		
hnh	A15	EP	0 673 895	A2	AT&T CORP.	09-27-1995		

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